

Sub D1  
C1  
C2

43. (Amended) A method of manufacturing a display device comprising the steps of:  
forming a thin film transistor over a substrate;  
forming a pixel electrode electrically connected to the thin film transistor;  
forming a body with a textured surface on the pixel electrode;  
forming a light reflection film on the body with the textured surface by one selected from  
the group consisting of a sputtering method, a coating method, and a vacuum evaporation method;  
and  
flattening a surface of the light reflection film by a CMP process.

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Sub D3  
C2

50. (Amended) A method of manufacturing a display device comprising the steps of:  
forming a thin film transistor over a substrate;  
forming a pixel electrode electrically connected to the thin film transistor;  
forming a body with a textured surface on the pixel electrode; and  
forming a light reflection film on the body with the textured surface by one selected from  
the group consisting of a sputtering method, a coating method, and a vacuum evaporation method,  
wherein the light reflection film has a higher refractive index than the body with the textured  
surface.

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Sub D4  
C3

57. (Amended) A method of manufacturing a display device comprising the steps of:  
forming an insulated gate field effect transistor on a semiconductor substrate;  
forming a pixel electrode electrically connected to the insulated gate field effect transistor;  
forming a body with a textured surface on the pixel electrode; and  
forming a light reflection film on the body with the textured surface by one selected from  
the group consisting of a sputtering method, a coating method, and a vacuum evaporation method.

D4  
C3  
cont

64. (Amended) A method of manufacturing a display device comprising the steps of:  
forming an insulated gate field effect transistor on a semiconductor substrate;  
forming a pixel electrode electrically connected to the insulated gate field effect transistor;  
forming a body with a textured surface on the pixel electrode;  
forming a light reflection film on the body with the textured surface by one selected from  
the group consisting of a sputtering method, a coating method, and a vacuum evaporation method;  
and  
flattening a surface of the light reflection film by a CMP process.

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Sub D6  
C4

71. (Amended) A method of manufacturing a display device comprising the steps of:  
forming an insulated gate field effect transistor on a semiconductor substrate;  
forming a pixel electrode electrically connected to the insulated gate field effect transistor;  
forming a body with a textured surface on the pixel electrode; and  
forming a light reflection film on the body with the textured surface by one selected from  
the group consisting of a sputtering method, a coating method, and a vacuum evaporation method,  
wherein the light reflection film has a higher refractive index than the body with the textured  
surface.

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#### REMARKS

In the Office Action, the Examiner rejects Claims 36-77 under the judicially created doctrine of double patenting over claims 1-81 of Application serial no. 09/329,597 (now U.S. Patent 6,384,886, a copy which is enclosed herewith). This rejection is respectfully traversed.

Applicants have now amended each of the independent claims pending in this application to include the limitation of "forming a light reflection film on the body with the textured surface by